



CSD17484F4 30 V N-Channel FemtoFET™ MOSFET

1 Features

- Low On-Resistance
- Ultra-Low Q_g and Q_{gd}
- Low Threshold Voltage
- Ultra-Small Footprint (0402 Case Size)
 - 1.0 mm × 0.6 mm
- Ultra-Low Profile
 - 0.2 mm Height
- Integrated ESD Protection Diode
 - Rated >4 kV HBM
 - Rated >2 kV CDM
- Lead and Halogen Free
- RoHS Compliant

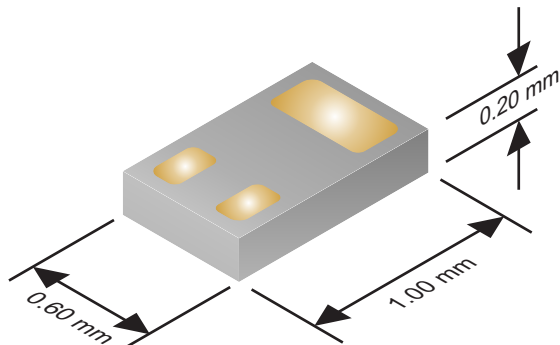
2 Applications

- Optimized for Load Switch Applications
- Optimized for General Purpose Switching Applications
- Battery Applications
- Handheld and Mobile Applications

3 Description

This 99 mΩ, 30 V N-Channel FemtoFET™ MOSFET is designed and optimized to minimize the footprint in many handheld and mobile applications. This technology is capable of replacing standard small signal MOSFETs while providing at least a 60% reduction in footprint size.

Typical Part Dimensions



Product Summary

$T_A = 25^\circ\text{C}$		TYPICAL VALUE	UNIT
V_{DS}	Drain-to-Source Voltage	30	V
Q_g	Gate Charge Total (4.5 V)	920	pC
Q_{gd}	Gate Charge Gate-to-Drain	75	pC
$R_{DS(on)}$	Drain-to-Source On-Resistance	$V_{GS} = 1.8\text{ V}$	170 mΩ
		$V_{GS} = 2.5\text{ V}$	125 mΩ
		$V_{GS} = 4.5\text{ V}$	107 mΩ
		$V_{GS} = 8.0\text{ V}$	99 mΩ
$V_{GS(th)}$	Threshold Voltage	0.85	V

Ordering Information⁽¹⁾

Device	Qty	Media	Package	Ship
CSD17484F4	3000	7-Inch Reel	Femto(0402) 1.0 mm × 0.6 mm	Tape and Reel
CSD17484F4T	250	7-Inch Reel	Land Grid Array (LGA)	

(1) For all available packages, see the orderable addendum at the end of the data sheet.

Absolute Maximum Ratings

$T_A = 25^\circ\text{C}$		VALUE	UNIT
V_{DS}	Drain-to-Source Voltage	30	V
V_{GS}	Gate-to-Source Voltage	12	V
I_D	Continuous Drain Current ⁽¹⁾	3.0	A
I_{DM}	Pulsed Drain Current ⁽¹⁾⁽²⁾	18	A
I_G	Continuous Gate Clamp Current	35	mA
	Pulsed Gate Clamp Current ⁽²⁾	350	
P_D	Power Dissipation	500	mW
ESD Rating	Human Body Model (HBM)	4	kV
	Charged Device Model (CDM)	2	kV
T_J, T_{stg}	Operating Junction and Storage Temperature Range	–55 to 150	°C
E_{AS}	Avalanche Energy, single pulse $I_D = 7.1\text{ A}$, $L = 0.1\text{ mH}$, $R_G = 25\text{ }\Omega$	2.5	mJ

(1) Typical $R_{\theta JA} = 85^\circ\text{C/W}$ on 1 inch² (6.45 cm²), 2 oz. (0.071 mm thick) Cu pad on a 0.06 inch (1.52 mm) thick FR4 PCB.

(2) Pulse duration $\leq 100\text{ }\mu\text{s}$, duty cycle $\leq 1\%$

Top View

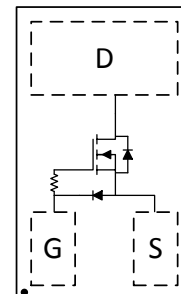


Table of Contents

1 Features	1	6.1 Trademarks	7
2 Applications	1	6.2 Electrostatic Discharge Caution	7
3 Description	1	6.3 Glossary	7
4 Revision History	2	7 Mechanical, Packaging, and Orderable Information	8
5 Specifications	3	7.1 Mechanical Dimensions	8
5.1 Electrical Characteristics	3	7.2 Recommended Minimum PCB Layout	9
5.2 Thermal Information	3	7.3 Recommended Stencil Pattern	9
5.3 Typical MOSFET Characteristics	4	7.4 CSD17484F4 Embossed Carrier Tape Dimensions	10
6 Device and Documentation Support	7		

4 Revision History

DATE	REVISION	NOTES
May 2015	*	Initial release.

5 Specifications

5.1 Electrical Characteristics

(T_A = 25°C unless otherwise stated)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT	
STATIC CHARACTERISTICS							
BV _{DSS}	Drain-to-Source Voltage	V _{GS} = 0 V, I _{DS} = 250 μA	30			V	
I _{DSS}	Drain-to-Source Leakage Current	V _{GS} = 0 V, V _{DS} = 24 V	100			nA	
I _{GSS}	Gate-to-Source Leakage Current	V _{DS} = 0 V, V _{GS} = 12 V	50			nA	
V _{GS(th)}	Gate-to-Source Threshold Voltage	V _{DS} = V _{GS} , I _{DS} = 250 μA	0.65	0.85	1.10	V	
R _{DS(on)}	Drain-to-Source On-Resistance	V _{GS} = 1.8 V, I _{DS} = 0.5 A	170			270	mΩ
		V _{GS} = 2.5 V, I _{DS} = 0.5 A	125			160	mΩ
		V _{GS} = 4.5 V, I _{DS} = 0.5 A	107			128	mΩ
		V _{GS} = 8 V, I _{DS} = 0.5 A	99			121	mΩ
		g _{fs}	Transconductance	V _{DS} = 15 V, I _{DS} = 0.5 A	4		
DYNAMIC CHARACTERISTICS							
C _{iss}	Input Capacitance	V _{GS} = 0 V, V _{DS} = 15 V, f = 1 MHz	150			195	pF
C _{oss}	Output Capacitance		44			57	pF
C _{rss}	Reverse Transfer Capacitance		2.2			2.9	pF
R _G	Series Gate Resistance	V _{DS} = 15 V, I _{DS} = 0.5 A	8				Ω
Q _g	Gate Charge Total (4.5 V)		920			1200	pC
Q _g	Gate Charge Total (8.0 V)		1570			2040	pC
Q _{gd}	Gate Charge Gate-to-Drain		75				pC
Q _{gs}	Gate Charge Gate-to-Source		280				pC
Q _{g(th)}	Gate Charge at V _{th}		140				pC
Q _{oss}	Output Charge		V _{DS} = 15 V, V _{GS} = 0 V	1400			
t _{d(on)}	Turn On Delay Time	V _{DS} = 15 V, V _{GS} = 4.5 V, I _{DS} = 0.5 A, R _G = 2 Ω	3				ns
t _r	Rise Time		1				ns
t _{d(off)}	Turn Off Delay Time		11				ns
t _f	Fall Time		4				ns
DIODE CHARACTERISTICS							
V _{SD}	Diode Forward Voltage	I _{SD} = 0.5 A, V _{GS} = 0 V	0.73			0.9	V
Q _{rr}	Reverse Recovery Charge	V _{DS} = 15 V, I _F = 0.5 A, di/dt = 300 A/μs	1300				pC
t _{rr}	Reverse Recovery Time		6.2				ns

5.2 Thermal Information

(T_A = 25°C unless otherwise stated)

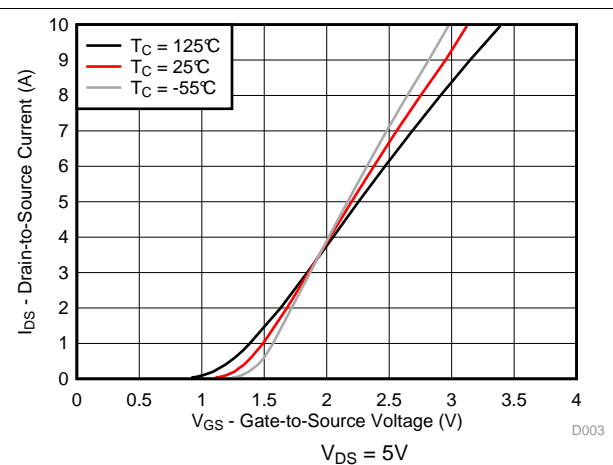
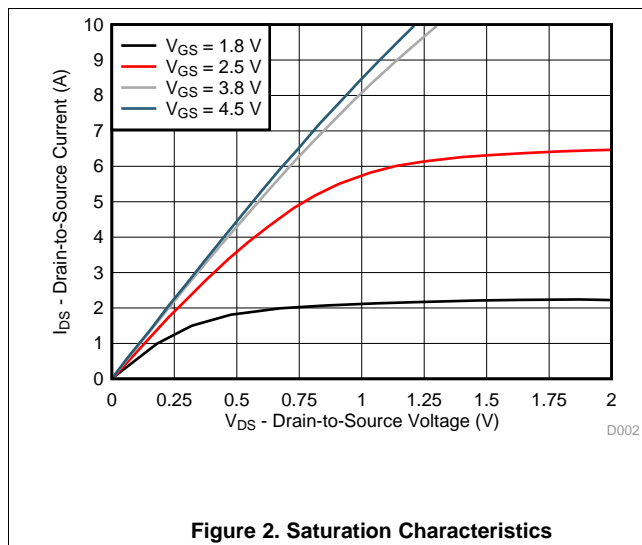
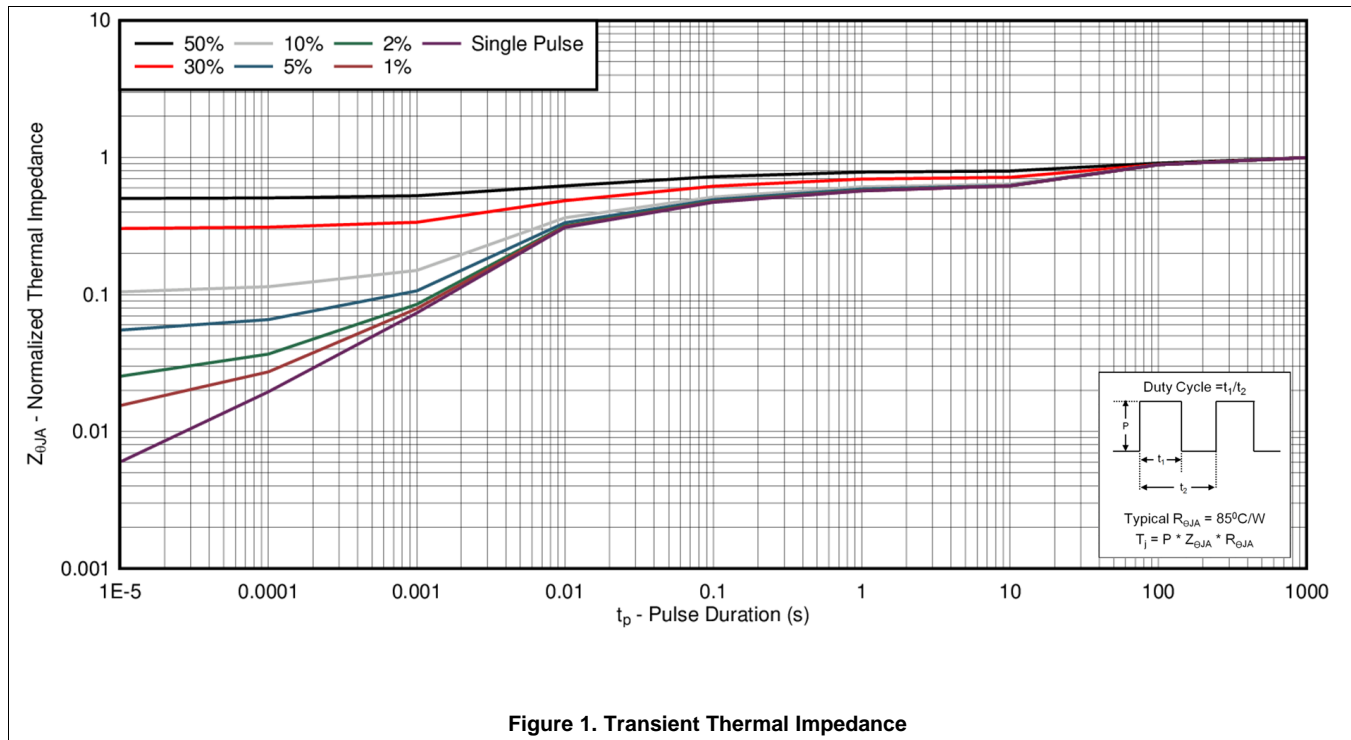
THERMAL METRIC		TYPICAL VALUES	UNIT
R _{θJA}	Junction-to-Ambient Thermal Resistance ⁽¹⁾	85	°C/W
	Junction-to-Ambient Thermal Resistance ⁽²⁾	245	

(1) Device mounted on FR4 material with 1 inch² (6.45 cm²), 2 oz. (0.071 mm thick) Cu.

(2) Device mounted on FR4 material with minimum Cu mounting area.

5.3 Typical MOSFET Characteristics

($T_A = 25^\circ\text{C}$ unless otherwise stated)



Typical MOSFET Characteristics (continued)

($T_A = 25^\circ\text{C}$ unless otherwise stated)

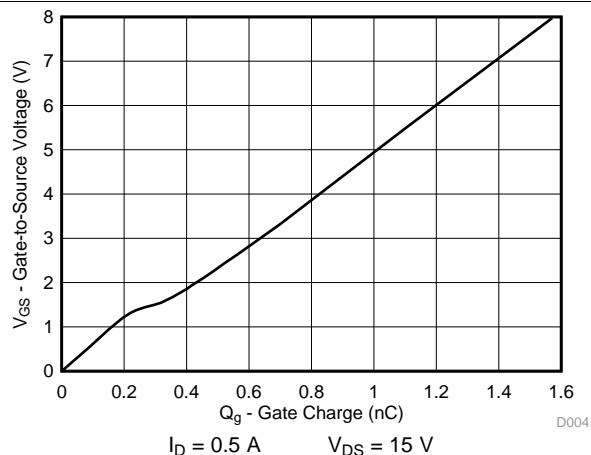


Figure 4. Gate Charge

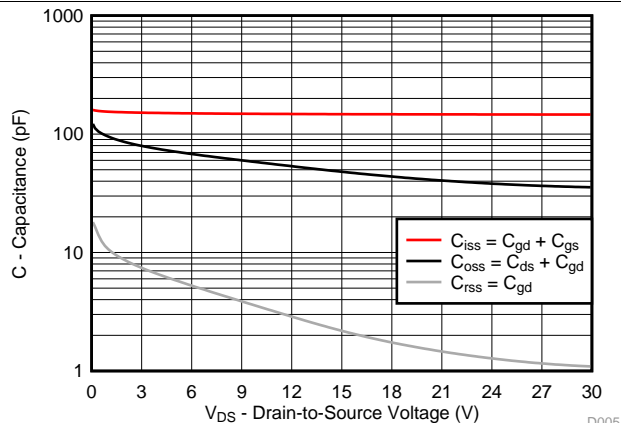


Figure 5. Capacitance

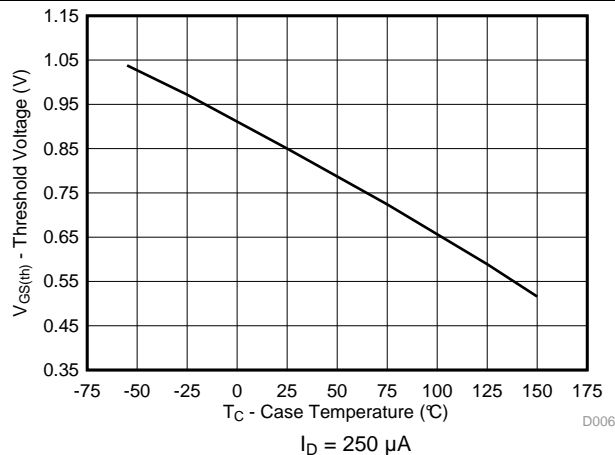


Figure 6. Threshold Voltage vs Temperature

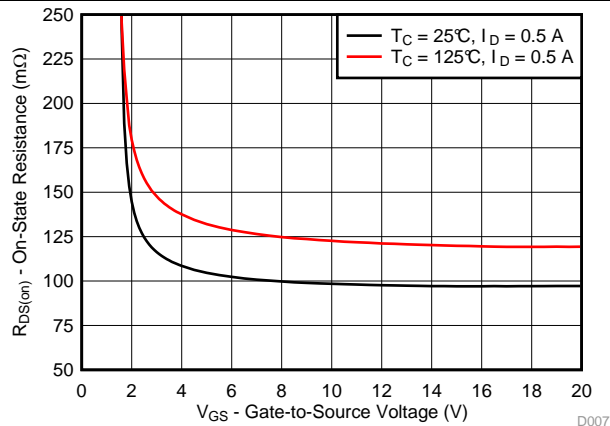


Figure 7. On-State Resistance vs Gate-to-Source Voltage

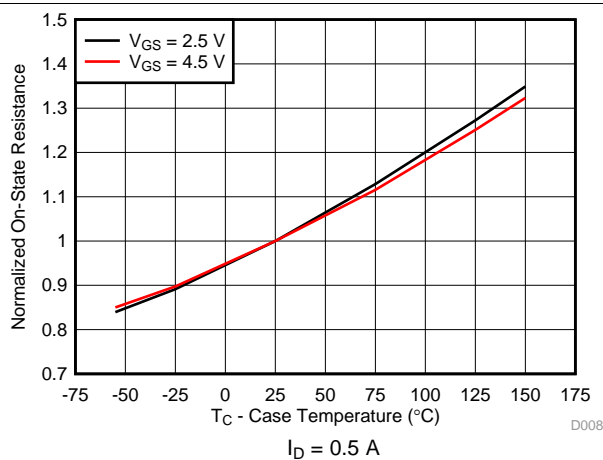


Figure 8. Normalized On-State Resistance vs Temperature

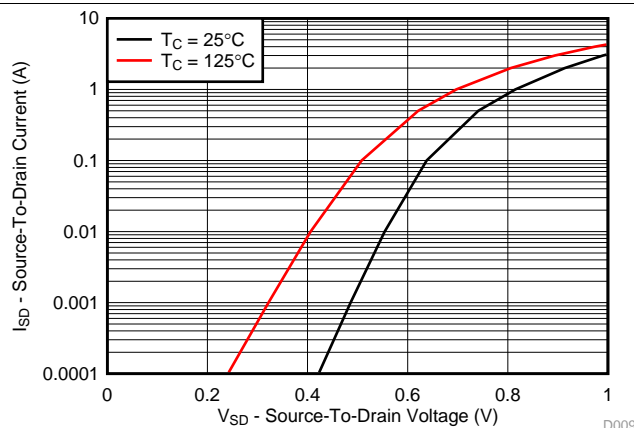


Figure 9. Typical Diode Forward Voltage

Typical MOSFET Characteristics (continued)

($T_A = 25^\circ\text{C}$ unless otherwise stated)

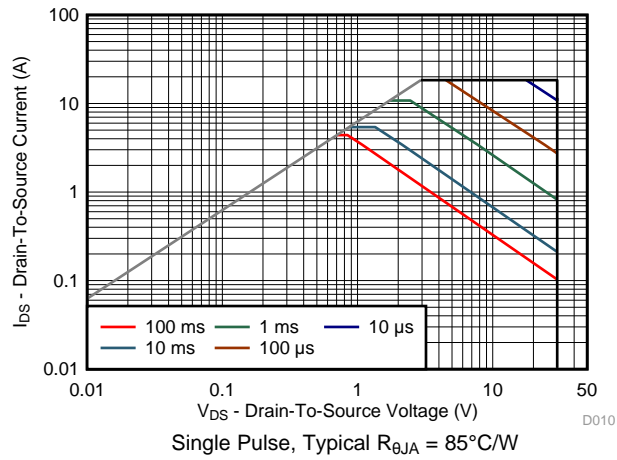


Figure 10. Maximum Safe Operating Area

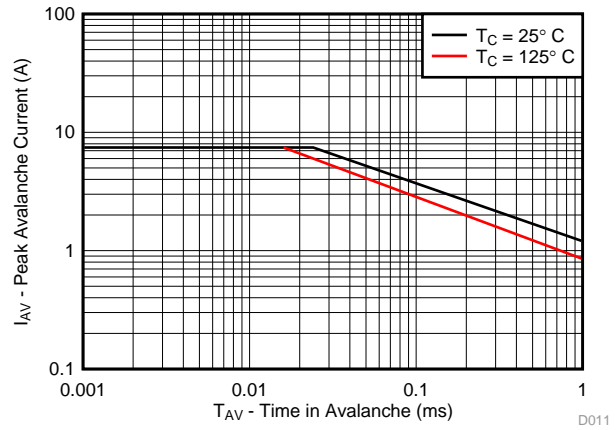


Figure 11. Single Pulse Unclamped Inductive Switching

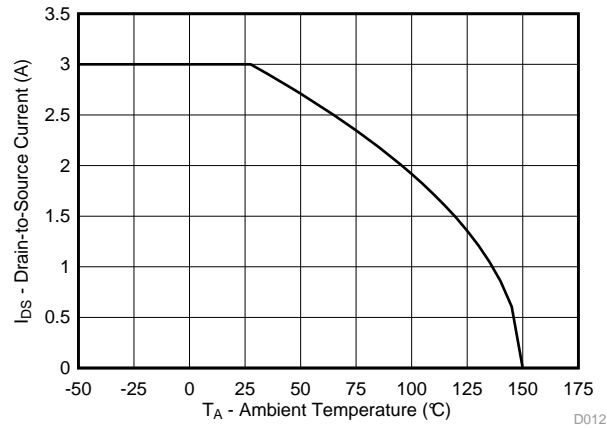


Figure 12. Maximum Drain Current vs Temperature

6 Device and Documentation Support

6.1 Trademarks

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6.2 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

6.3 Glossary

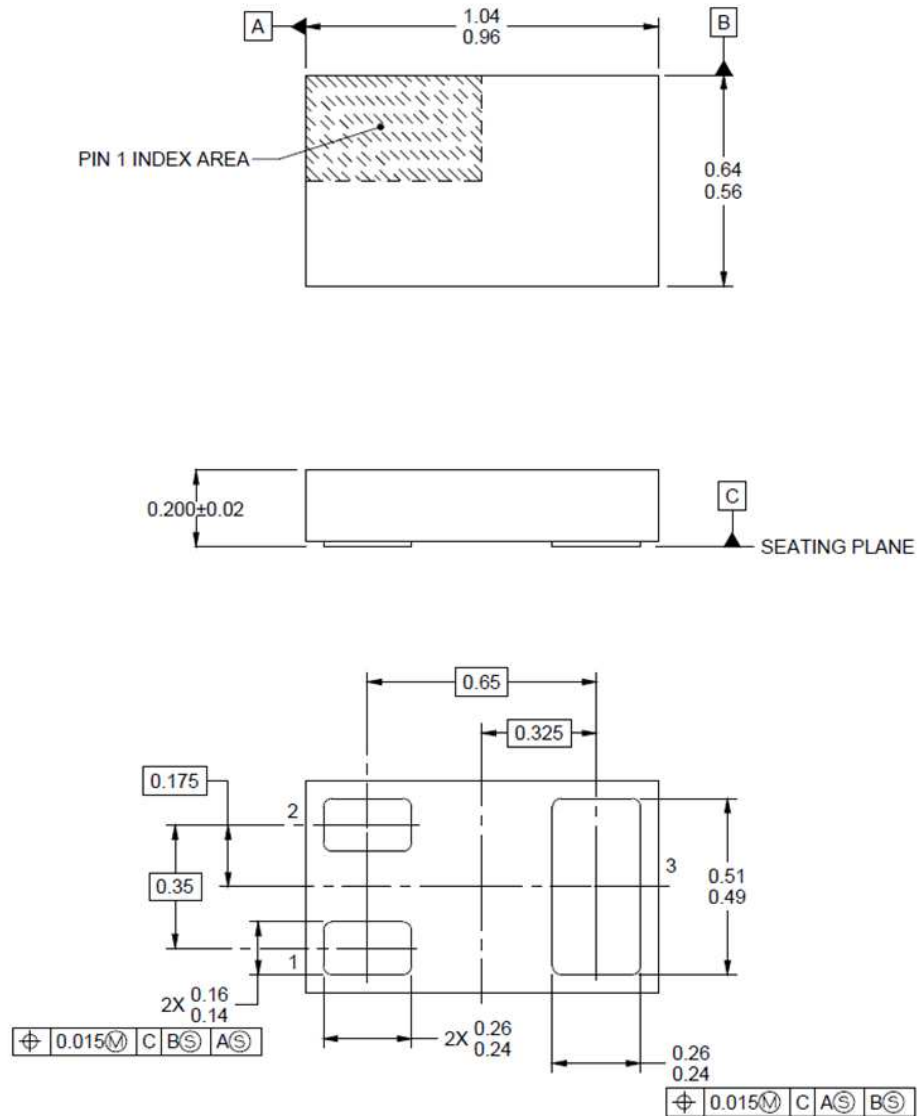
[SLYZ022](#) — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

7 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

7.1 Mechanical Dimensions

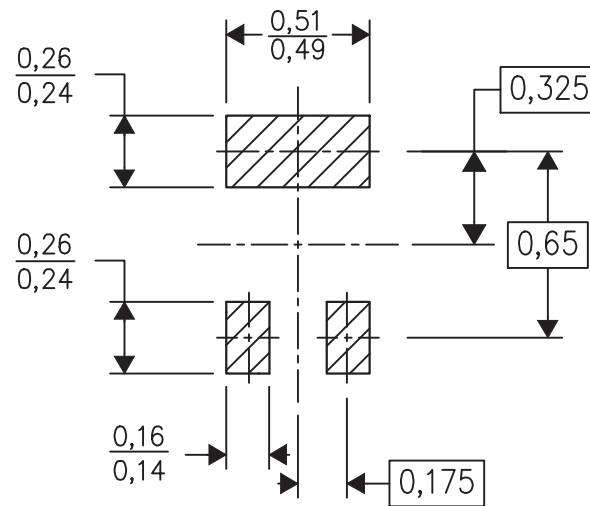


- (1) All linear dimensions are in millimeters (dimensions and tolerancing per AME T14.5M-1994).
- (2) This drawing is subject to change without notice.
- (3) This package is a PB-free solder land design.

Pin Configuration

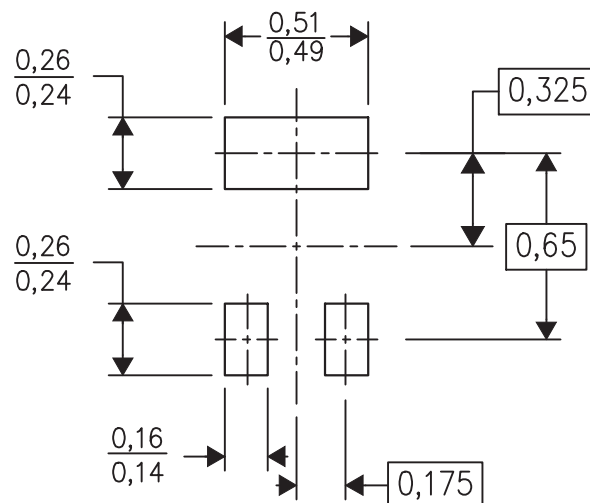
Position	Designation
Pin 1	Gate
Pin 2	Source
Pin 3	Drain

7.2 Recommended Minimum PCB Layout



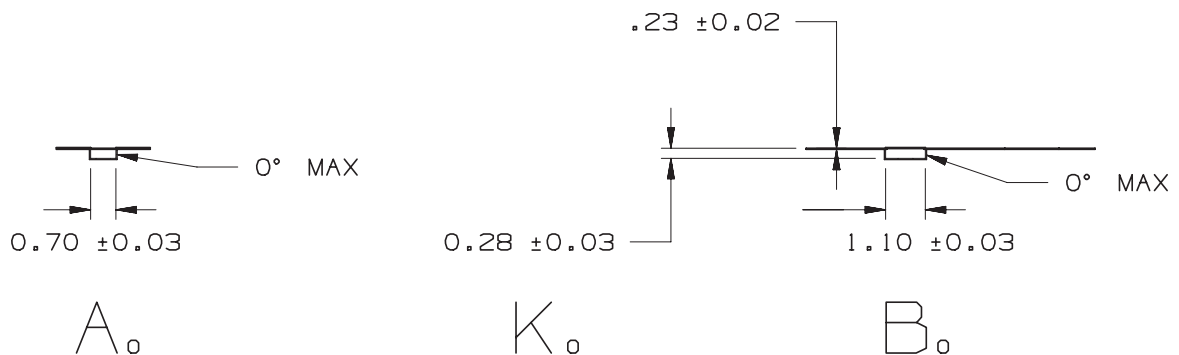
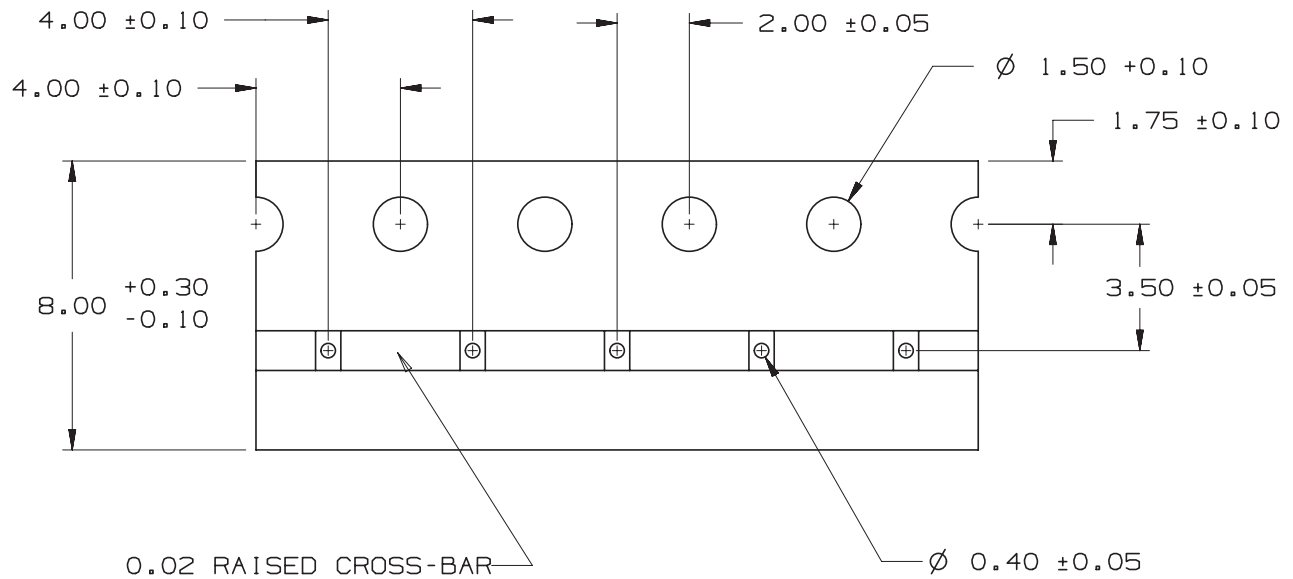
(1) All dimensions are in millimeters.

7.3 Recommended Stencil Pattern



(1) All dimensions are in millimeters.

7.4 CSD17484F4 Embossed Carrier Tape Dimensions



- (1) Pin 1 is oriented in the top-right quadrant of the tape enclosure (quadrant 2), closest to the carrier tape sprocket holes.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
CSD17484F4	ACTIVE	PICOSTAR	YJJ	3	3000	Green (RoHS & no Sb/Br)	Call TI	Level-1-260C-UNLIM	-55 to 150	YG2	Samples
CSD17484F4T	ACTIVE	PICOSTAR	YJJ	3	250	Green (RoHS & no Sb/Br)	Call TI	Level-1-260C-UNLIM	-55 to 150	YG2	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check <http://www.ti.com/productcontent> for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

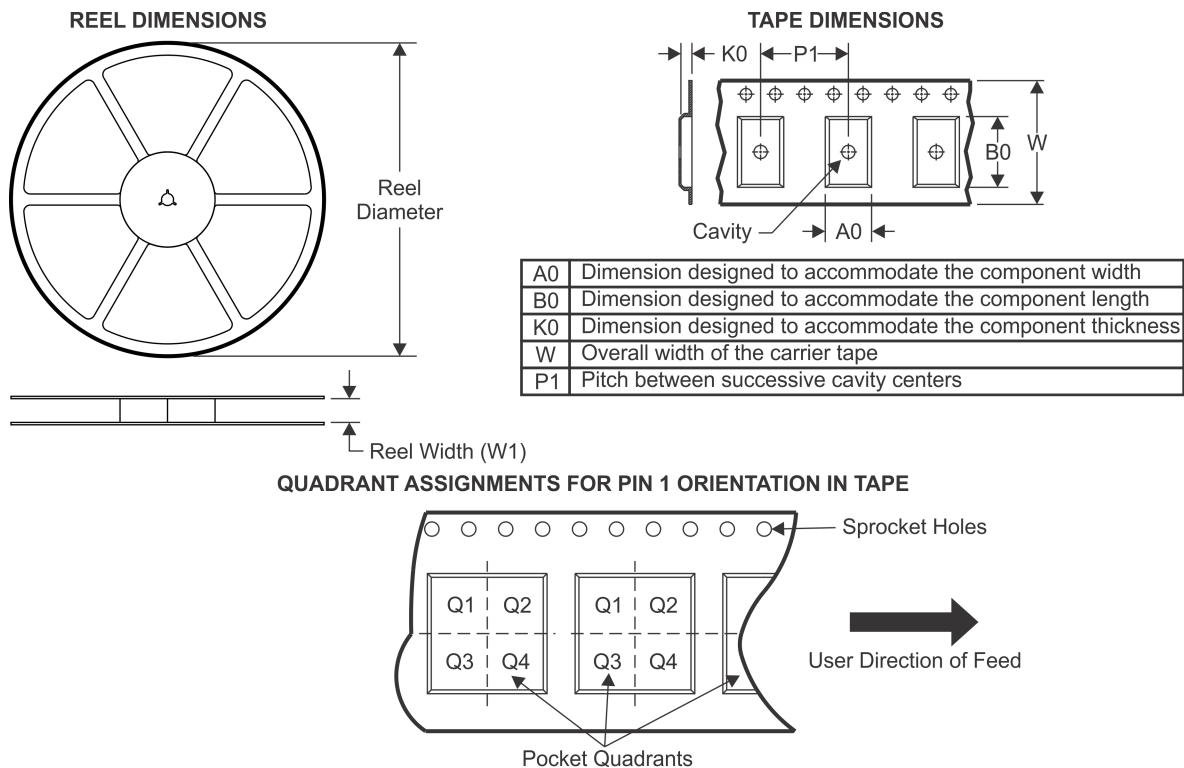
(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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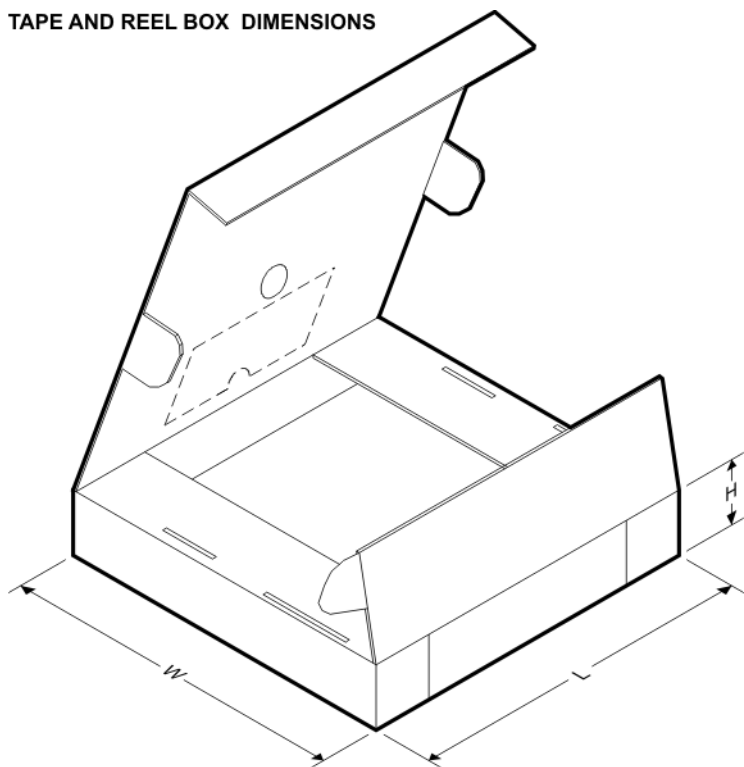
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TAPE AND REEL INFORMATION


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CSD17484F4	PICOST AR	YJJ	3	3000	178.0	9.2	0.7	1.1	0.28	4.0	8.0	Q2

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CSD17484F4	PICOSTAR	YJJ	3	3000	220.0	220.0	35.0

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